

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 100 A, 1700 V, D1, Die

NDC100170A, NDCTR100170A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 2045 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

Applications

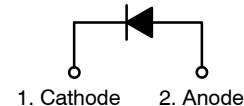
- Industrial Motor Loads, Wind Generation Inverter, Solar Inverter, UPS
- Power Switching Circuits

Die Information

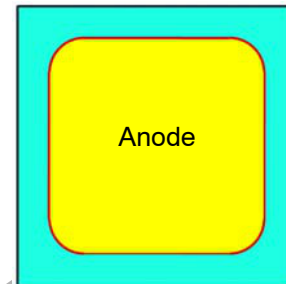
- Wafer Diameter: 6 inch
- Die Size: 6140 × 9500 μm (include Scribe Lane)
- Metallization:
 - ♦ Top: Ti/TiN/AlSiCu
 - ♦ Back: Ti/NiV/Ag
- Die Thickness: Typ. 200 μm
- Bonding Pad Size:
 - ♦ Anode: 4260 × 7620 μm
- Recommended Wire Bond (Note 1)
 - ♦ Anode: 20 mil × 3

NOTE:

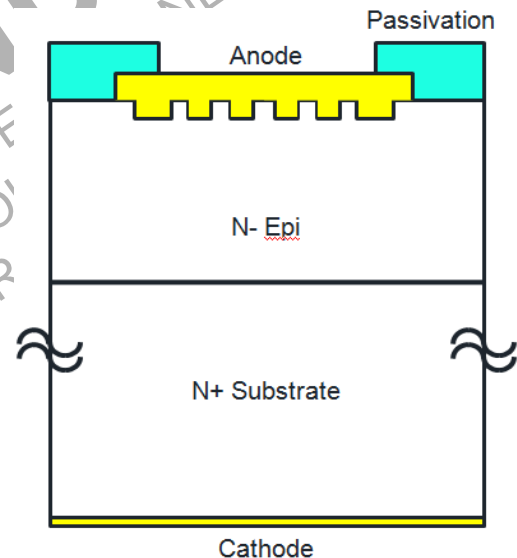
1. Based on TO-247 package



Schottky Diode



CROSS SECTION



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

NDC100170A, NDCTR100170A

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		1700	V
E _{AS}	Single Pulse Avalanche Energy (Notes 2 and 4)		2025	mJ
I _F	Continuous Rectified Forward Current @ T _C < 153°C		100	A
	Continuous Rectified Forward Current @ T _C < 135°C		145	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1435	A
		T _C = 150°C, 10 μs	1428	A
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	574	A
P _{tot}	Power Dissipation	T _C = 25°C	1666	W
		T _C = 150°C	277	W
T _J , T _{STG}	Operating and Storage Temperature Range		−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. E_{AS} of 2025 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 90 A, V = 50 V.

3. I_{F, Max}, and I_{F, SM} surge test value are limited by measurement limitation, it's not product capability

4. DC, E_{AS} and Curve test result base on TO247 package

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max	0.09	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

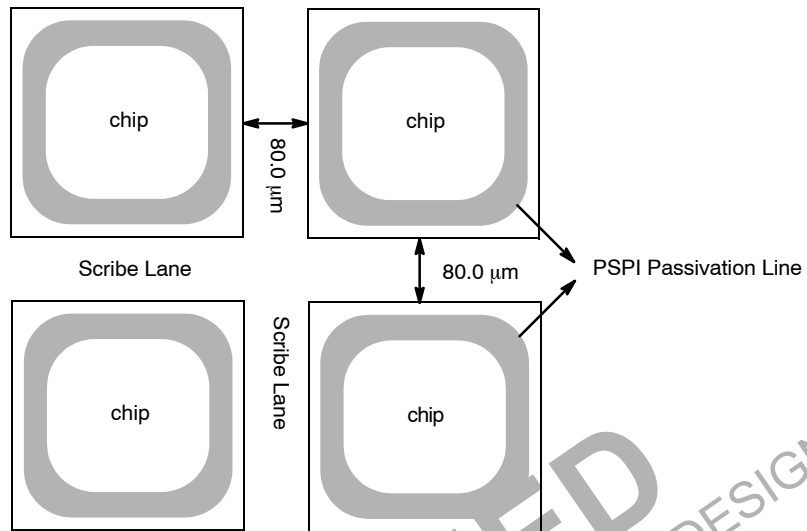
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 100 A, T _J = 25°C	–	1.6	–	V
		I _F = 100 A, T _J = 125°C	–	2.16	–	
		I _F = 100 A, T _J = 175°C	–	2.6	–	
I _R	Reverse Current	V _R = 1700 V, T _J = 25°C	–	0.15	40	μA
		V _R = 1700 V, T _J = 125°C	–	1.45	60	
		V _R = 1700 V, T _J = 175°C	–	12.3	100	
Q _C	Total Capacitive Charge	V = 800 V	–	604	–	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	–	7672	–	pF
		V _R = 400 V, f = 100 kHz	–	539	–	
		V _R = 800 V, f = 100 kHz	–	383	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NDC100170A, NDCTR100170A

The Configuration of Chips

(Based on 6 inch Wafer)



Sawn-on-film frame packing based on tested wafer

ORDERING INFORMATION

Part Number	Die Size with SL (μm)	Package	Shipping
NDC100170A	6140*9500	N/A	Wafer Sales
NDCTR100170A	6140*9500	N/A	Tape & Reel

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

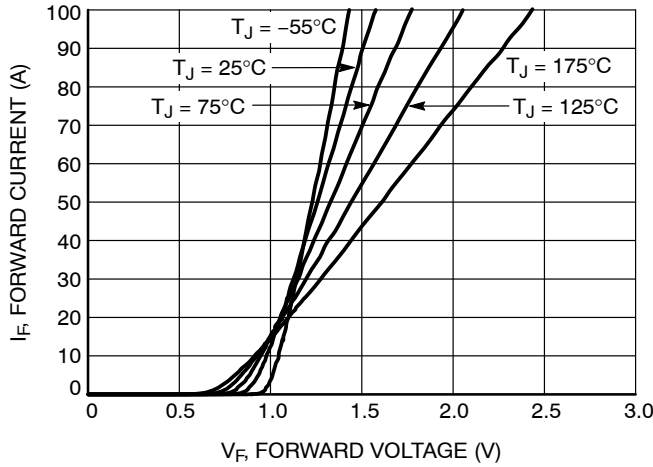


Figure 1. Forward Characteristics

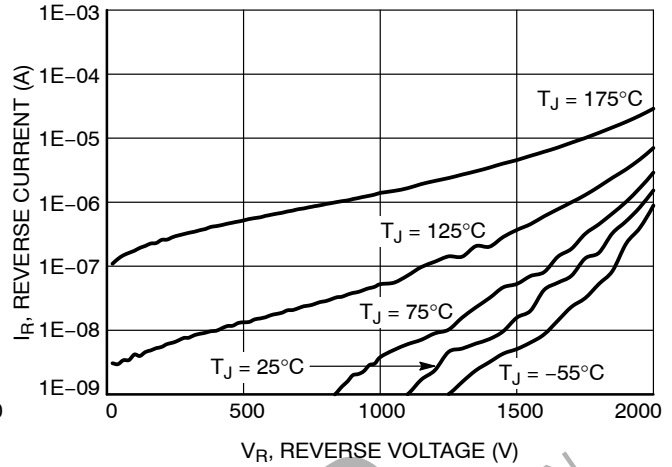


Figure 2. Reverse Characteristics

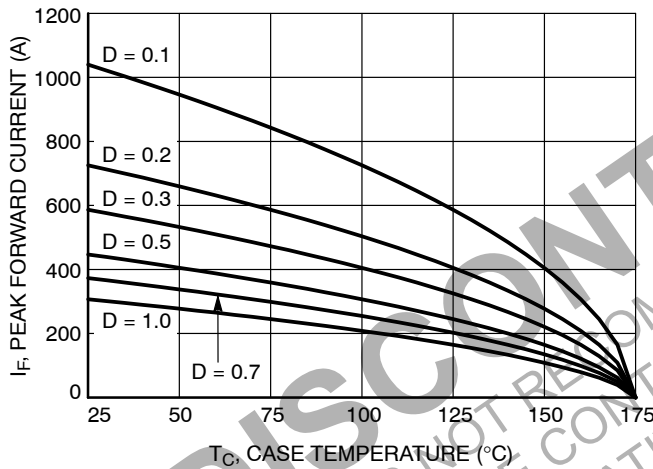


Figure 3. Current Derating

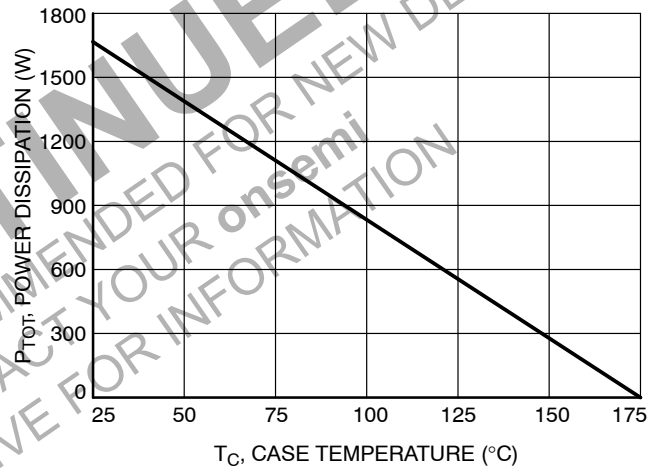


Figure 4. Power Derating

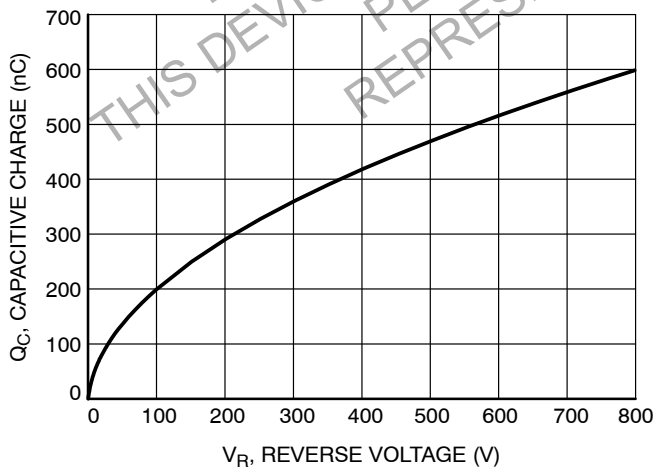


Figure 5. Capacitive Charge vs. Reverse Voltage

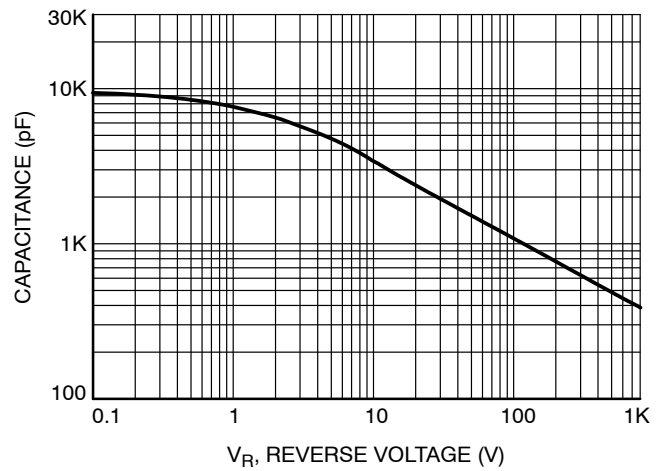


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

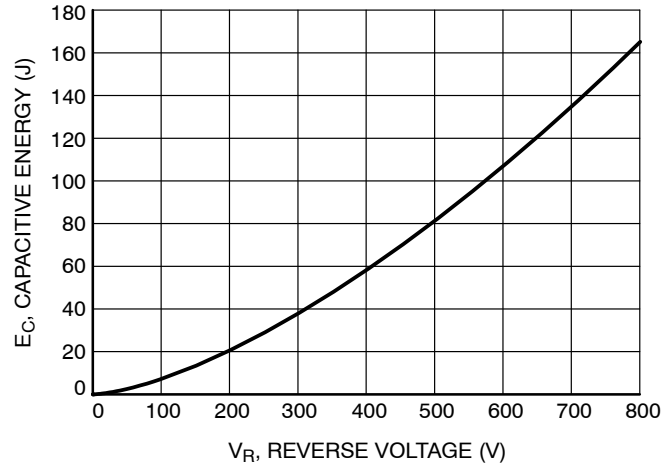


Figure 7. Capacitance Stored Energy

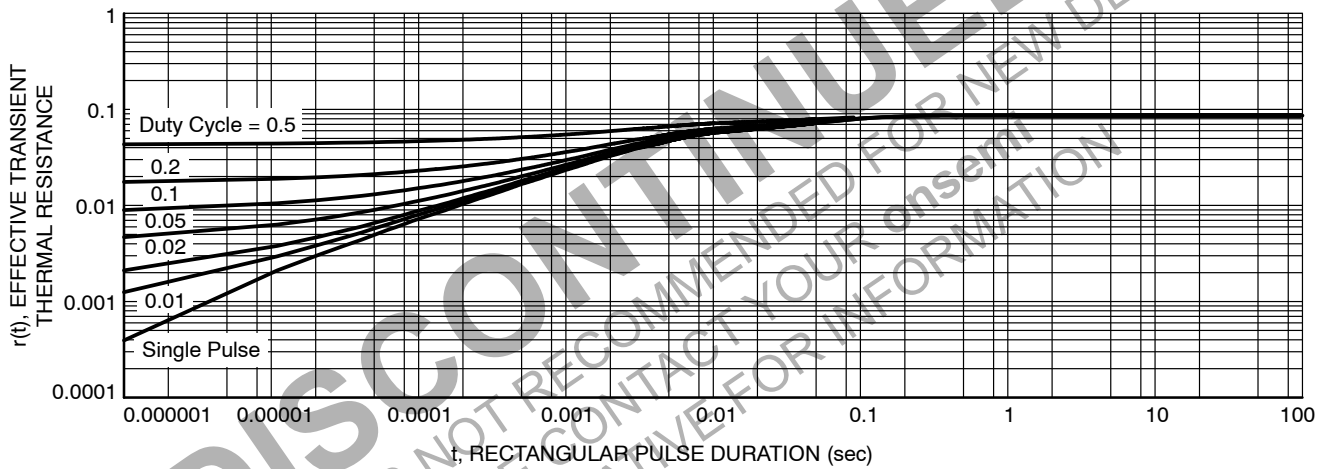


Figure 8. Junction-to-Case Transient Thermal Response

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales